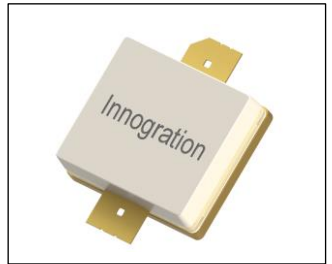




## GaN HEMT 28V, HF-1.5GHz 65W, RF Power Transistor

### Description

The STBH15065A2C is a 65W GaN HEMT, designed for multiple applications up to 1.5GHz. It can be used in CW, Pulse and any other modulation modes. There is no guarantee of performance when this part is used in applications designed Outside of these frequencies.



- Typical class AB RF Performance with device soldered

$V_{ds}=28V$ ,  $I_{dq}=100mA$ , CW

Freq (MHz)	P1dB (dBm)	P1dB (W)	P1dB Eff (%)	P1dB Gain (dB)	P3dB (dBm)	P3dB (W)	P3dB Eff (%)
650	47.7	58.9	64.2	18.41	48.15	65.2	66.6
700	47.88	61.4	63.5	19.1	48.33	68.1	64.8
750	47.45	55.7	58.3	18.64	48.03	63.6	60.0
800	47.52	56.5	57.3	18.74	48.55	71.6	63.7
830	48.22	66.3	63.1	18.58	49	79.5	68.5
860	48.56	71.9	67.0	18.06	49.13	81.9	70.5

### Applications

- L band power amplifier
- P band power amplifier
- ISM/RF Energy power amplifier

### Important Note: Proper Biasing Sequence for GaN HEMT Transistors

#### Turning the device ON

1. Set VGS to the pinch-off (VP) voltage, typically -5 V
2. Turn on VDS to nominal supply voltage
3. Increase VGS until IDS current is attained
4. Apply RF input power to desired level

#### Turning the device OFF

1. Turn RF power off
2. Reduce VGS down to VP, typically -5 V
3. Reduce VDS down to 0 V
4. Turn off VGS

**Table 1. Maximum Ratings**

Rating	Symbol	Value	Unit
Drain--Source Voltage	$V_{DS}$	+200	Vdc
Gate--Source Voltage	$V_{GS}$	-8 to +0.5	Vdc
Operating Voltage	$V_{DD}$	50	Vdc
Maximum gate current	$I_{gs}$	16.8	mA
Storage Temperature Range	$T_{stg}$	-65 to +150	°C
Case Operating Temperature	$T_c$	+150	°C
Operating Junction Temperature	$T_J$	+225	°C

**Table 2. Thermal Characteristics**

Characteristic	Symbol	Value	Unit
Thermal Resistance, Junction to Case by FEA $T_c=85^{\circ}C$ , at $P_{diss}=30W$	$R_{\theta JC}$	2.8	°C /W



**Table 3. Electrical Characteristics (TA = 25°C unless otherwise noted)**

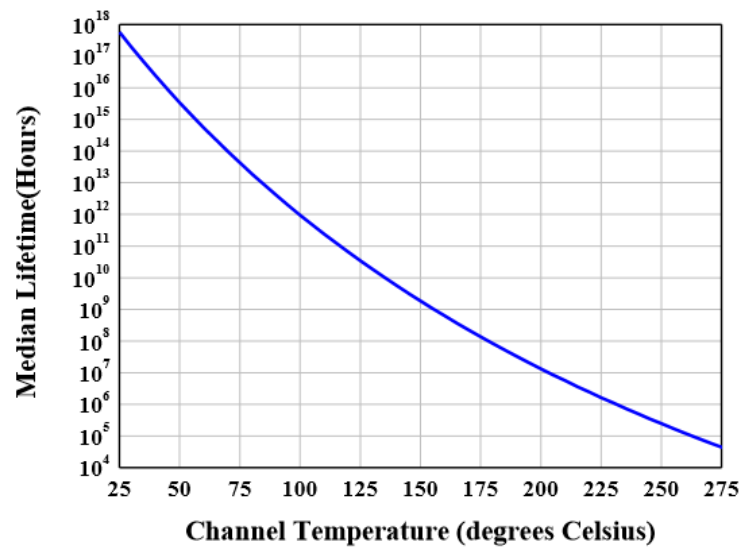
**DC Characteristics ( measured on wafer prior to packaging)**

Characteristic	Conditions	Symbol	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	VGS=-8V; IDS=16.8mA	V <sub>DSS</sub>		200		V
Gate Threshold Voltage	VDS =10V, ID = 16.8mA	V <sub>GS(th)</sub>	-4		-2	V
Gate Quiescent Voltage	VDS =28V, IDS=100mA, Measured in Functional Test	V <sub>GS(Q)</sub>		-3.3		V

**Ruggedness Characteristics**

Characteristic	Conditions	Symbol	Min	Typ	Max	Unit
Load mismatch capability	1.5GHz, Pout=65W Pulsed CW  All phase,  No device damages	VSWR		10:1		

**Figure 2: Median Lifetime vs. Channel Temperature**





## 650-860MHz Typical performance

Figure 3: Network analyzer output S11/S21

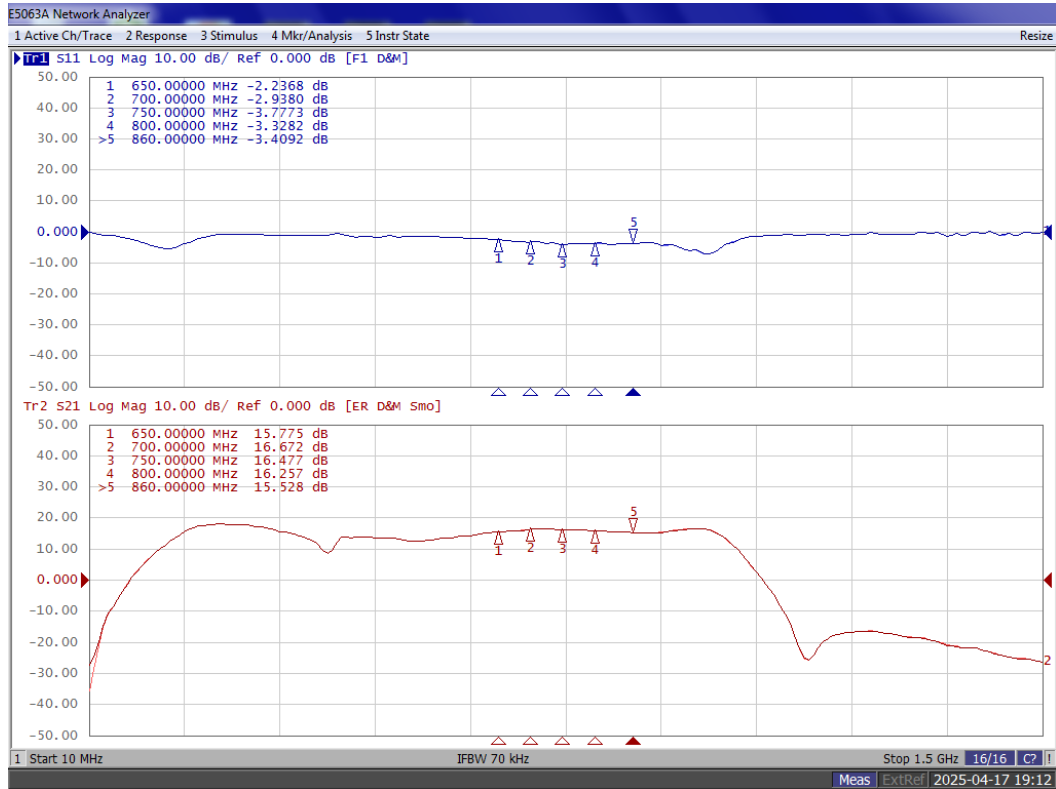
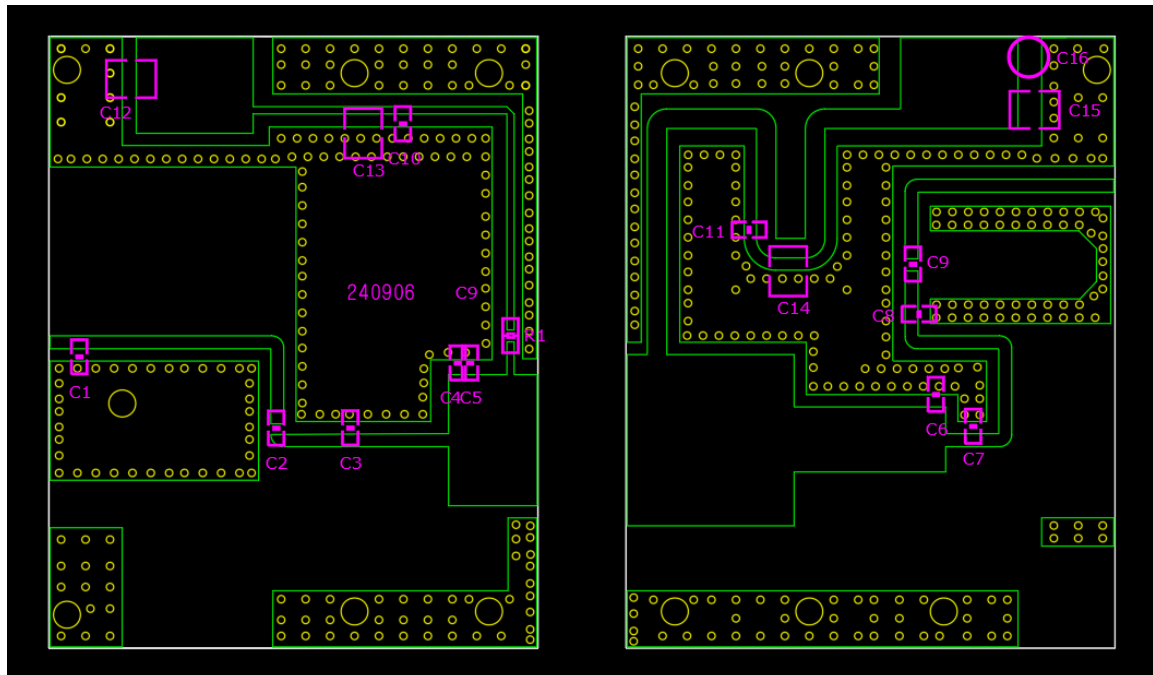


Figure 4: Picture of application board

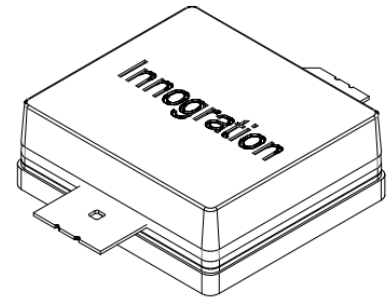
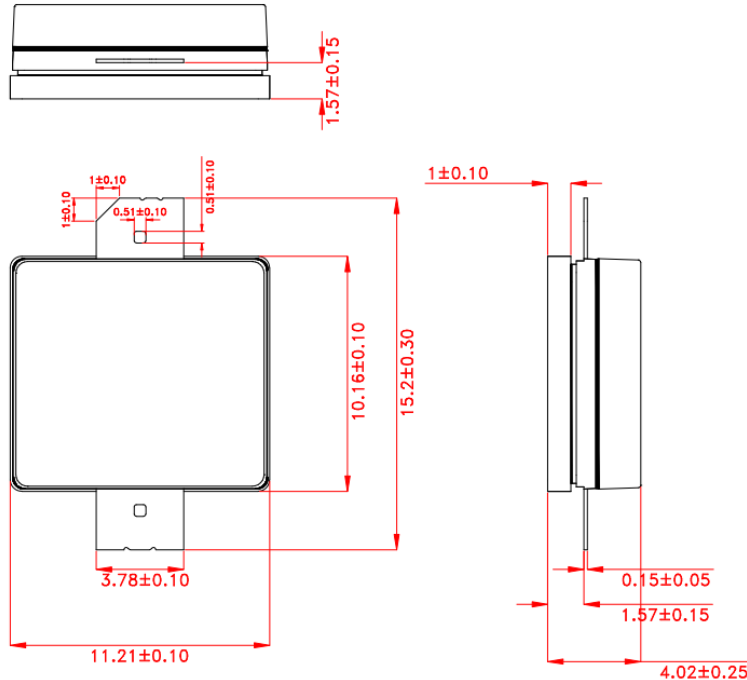




Reference	Footprint	Value	Quantity
C1,	0805	2.4pF	1
C2	0805	36pF	1
C3	0805	15pF	1
C4	0805	6.8pF	1
C5	0805	15pF	1
C6	0805	2.2pF	1
C7	0805	0.3pF	1
C8	0805	3pF	1
C9、C10、C11	0805	120pF	3
C12、C13、C14、C15	1210	10uF/63V	4
C16		470uF/63V	1
R1	0603	10ohm	1
PCB	RO4350B	20mils	



## Package Dimensions (Unit:mm)



Unit:mm

Tolerance ±0.10mm, Except as Noted.

## Revision history

Table 4. Document revision history

Date	Revision	Datasheet Status
2025/4/17	V1.0	Preliminary Datasheet Creation

Application data based on: ZYX-25-09

## Notice

Specifications are subject to change without notice. Innegration believes the information within the data sheet to be reliable. Innegration makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose.

“Typical” parameter is the average values expected by Innegration in quantities and are provided for information purposes only. It can and do vary in different applications and related performance can vary over time. All parameters should be validated by customer’s technical experts for each application.

Innegration products are not designed, intended or authorized for use as components in applications intended for surgical implant into the body or to support or sustain life, in applications in which the failure of the Innegration product could result in personal injury or death or in applications for planning, construction, maintenance or direct operation of a nuclear facility.

For any concerns or questions related to terms or conditions, please check with Innegration and authorized distributors

Copyright © by Innegration (Suzhou) Co.,Ltd.